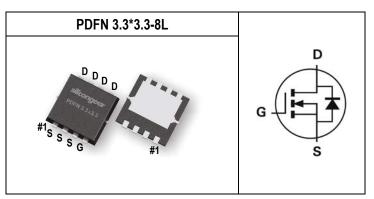


SG100N07E

Parameter	Value	Unit
VDSS	100	V
$R_{DS(ON) max.} V_{GS}$ =10V	27	mΩ
$R_{DS(ON) max.} V_{GS}$ =4.5V	31	mΩ
l <sub>D</sub>	24	А
Qg	59	nC
$Q_{gd}$	9	nC
Qsw	17.4	nC



Application
Motor / Body Load Control
Automotive Systems
Load Switch
DC-DC converters and Off-line UPS

## **Ordering Information**

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG100N07E	Halogen-Free	PDFN 3.3*3.3-8L	Е	Tape & Reel	5,000

#### Absolute Maximum Ratings (T\_=25°C unless otherwise noted)

	Parameter					
Drain-Source Voltage	V <sub>DS</sub>	100	V			
Gate-Source Voltage		V <sub>GS</sub>	±20	V		
Drain Current-Continuous Note 1	Tc=25°C	la la	24	А		
Drain Current-Continuous note	T <sub>c</sub> =100°C	ID	15	Α		
Drain Current-Pulsed Note 2	Tc=25°C	Ідм	49	Α		
Avalanche Current		lar	16	Α		
Single Pulse Avalanche Energy Note 3		E <sub>AS</sub>	13	mJ		
Maximum Dawar Dissinction	Tc=25°C	D-	48	W		
Maximum Power Dissipation	Tc=100°C	<i>P</i> <sub>D</sub>	19	W		
Operating and Storage Temperature Range		Tj, Tstg	-55 to 150	°C		

### **Thermal Resistance Ratings**

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Junction-to-Ambient Note 4	$R_{ heta JA}$	Steady State	-	-	32	°C/W
Thermal resistance, Junction-to-Case Note 4	Rөлс	Steady State	-	-	1.56	°C/W

#### Notes:

1. Limited by silicon chip capability and junction temperature.

2. Must be ensure junction temperature does not exceed 150-degree C. (Pulse Width  $\leq$  100uS, Duty  $\leq$  2%)

3. Limited by  $T_{Jmax}$ , starting  $T_J=25^{\circ}C$ , L=0.1mH, Rg=25 $\Omega$ , ID=25A, VGS=10V.

4. R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>0JC</sub> is guaranteed by design while R<sub>0JA</sub> is determined by the user's board design. R<sub>0JA</sub> shown below for single device operation on FR-4 in still air.



## Electrical Characteristics (TJ=25°C unless otherwise noted)

STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	V(BR)DSS	V <sub>GS</sub> =0V, I <sub>DS</sub> =250µA	100	-	-	V
	1	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	μA
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	-	-	100	μA
Gate-Body Leakage	lgss	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA

### STATIC CHARACTERISTICS

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250µA	1.2	1.7	2.4	V
Drain-Source On-State Resistance	Rds(ON)	V <sub>GS</sub> =10V, I <sub>DS</sub> =10A	-	22	27	mΩ
Drain-Source On-State Resistance	Rds(ON)	V <sub>GS</sub> =4.5V, I <sub>DS</sub> =6A	-	24	31	mΩ
Gate Resistance	$R_{g}$	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	-	0.5	1	Ω
Forward Transconductance	<b>G</b> fs	V <sub>DS</sub> =5V, I <sub>DS</sub> =20A	-	19	-	S

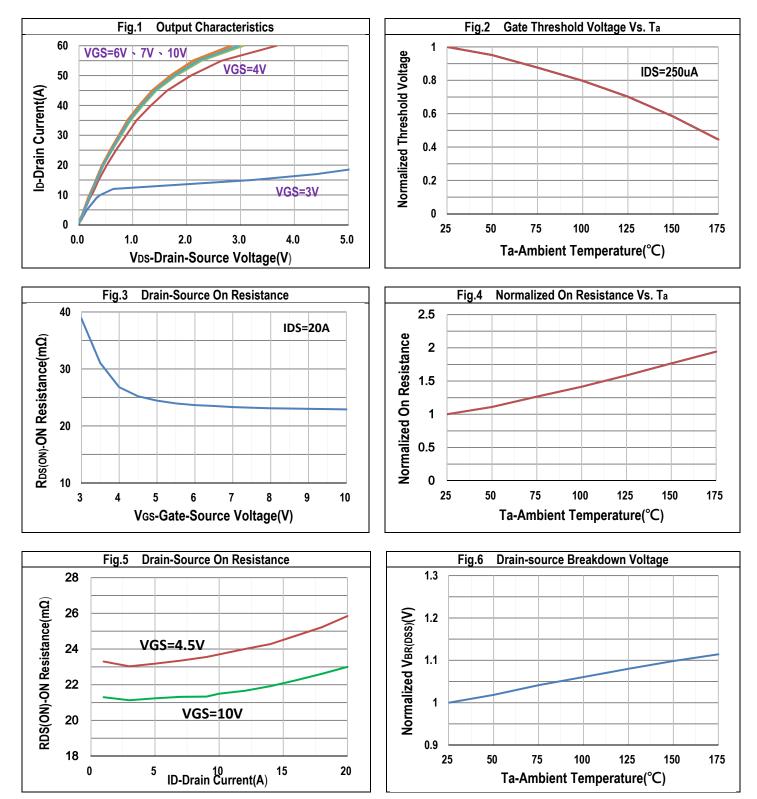
DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz	-	3205	-	pF
Output Capacitance	Coss	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz	-	94	-	pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz	-	55	-	pF
Turn-On Delay Time	T <sub>d(on)</sub>	$V_{DS}$ =50V, $V_{GS}$ =10V, $I_{DS}$ =20A, $R_{GEN}$ =3 $\Omega$	-	11	-	ns
Rise Time	tr	$V_{DS}$ =50V, $V_{GS}$ =10V, $I_{DS}$ =20A, $R_{GEN}$ =3 $\Omega$	-	26	-	ns
Turn-Off Delay Time	T <sub>d(off)</sub>	$V_{DS}$ =50V, $V_{GS}$ =10V, $I_{DS}$ =20A, $R_{GEN}$ =3 $\Omega$	-	34	-	ns
Fall Time	t <sub>f</sub>	$V_{DS}$ =50V, $V_{GS}$ =10V, $I_{DS}$ =20A, $R_{GEN}$ =3 $\Omega$	-	25	-	ns

GATE CHARGE CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate to Source Gate Charge	Qgs	$V_{DD}$ =50V, $I_D$ =20A, $V_{GS}$ =0 to 10V	-	14.6	-	nC
Gate charge at threshold	Qg(th)	$V_{DD}$ =50V, $I_D$ =20A, $V_{GS}$ =0 to 10V	-	6.2	-	nC
Gate to Drain Charge	$Q_{gd}$	$V_{DD}$ =50V, $I_D$ =20A, $V_{GS}$ =0 to 10V	-	9	-	nC
Switching charge	Qsw	$V_{DD}$ =50V, $I_D$ =20A, $V_{GS}$ =0 to 10V	-	17.4	-	nC
Gate charge total	$Q_g$	$V_{DD}$ =50V, $I_D$ =20A, $V_{GS}$ =0 to 10V	-	59	-	nC
Gate charge total	$Q_g$	$V_{DD}$ =50V, $I_D$ =20A, $V_{GS}$ =0 to 4.5V	-	32	-	nC
Gate plateau voltage	Vplateau	V <sub>DD</sub> =50V, I <sub>D</sub> =20A, V <sub>GS</sub> =0 to 10V	-	3.8	-	V
Gate charge total, sync. FET (Qg- Qgd)	Qg(sync)	V <sub>DS</sub> =0.1V, V <sub>GS</sub> =0 to 10V	-	50	-	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Diode continuous forward current (Body Diode)	ls	Tc=25°C	-	-	24	А	
Diode pulse current (Body Diode)	I <sub>SM</sub>	T <sub>C</sub> =25°C	-	-	49	Α	
Diode Forward Voltage	Vsd	V <sub>GS</sub> =0V, I <sub>S</sub> =1A	-	0.7	1	V	
Body Diode Reverse Recovery Time	trr	V <sub>DD</sub> =50V, I <sub>F</sub> =20A, di/dt=200A/µs	-	23	-	ns	
Body Diode Reverse Recovery Charge	Qrr	V <sub>DD</sub> =50V, I <sub>F</sub> =20A, di/dt=200A/µs	-	59	-	nC	

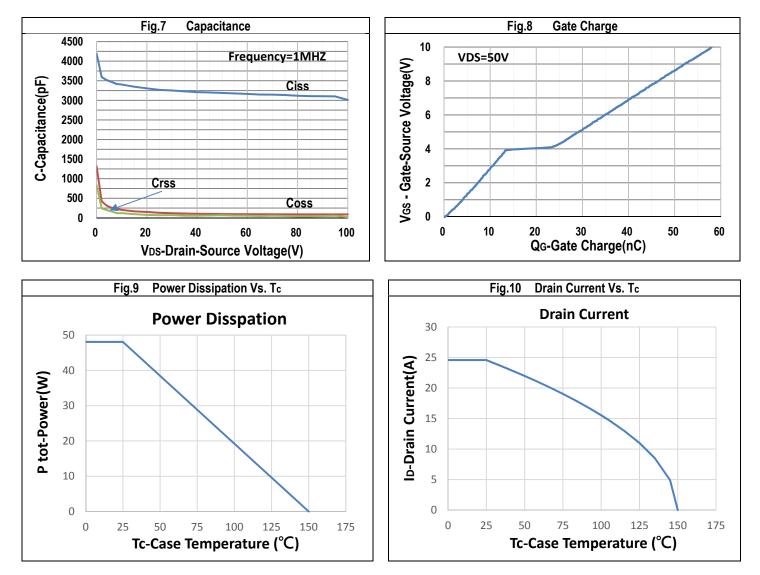


# **Typical Operating Characteristics**





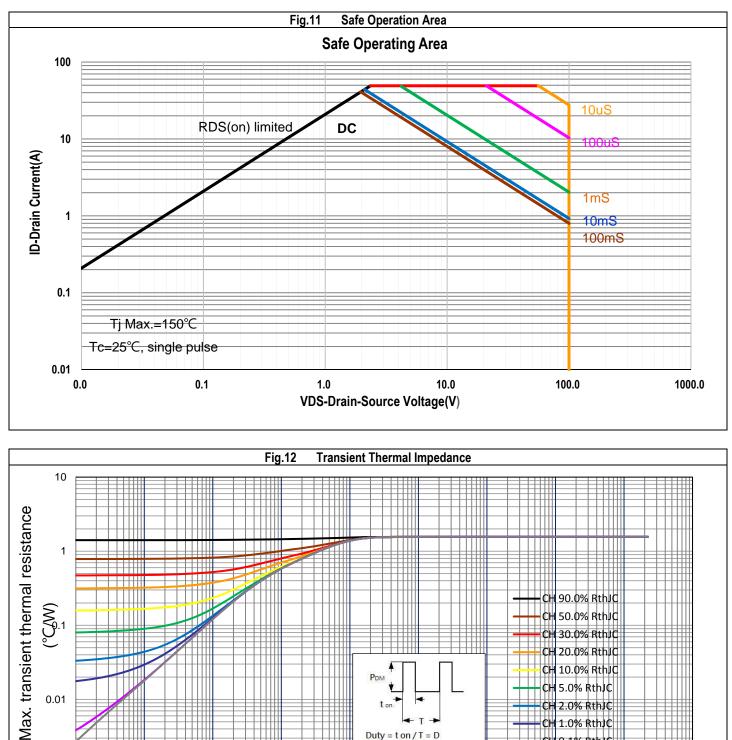
# **Typical Operating Characteristics (Cont.)**





# **SG100N07E**

**100V N-Channel Power MOSFET** 



Single pulse

1.E-04

1.E-03

1.E-05

∭0.1 0000

0.01

0.001

1.E-06

1.E+02

1.E+03

90.0% RthJC

50.0% RthJC 30.0% RthJC

20.0% RthJC

5.0% RthJC

1.0% RthJC

CH 10.0% RthJC

CH 2.0% RthJC

CH 0.1% RthJC

CH 0.0% RthJC

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CH

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СН

1.E+01

1.E-02

Duty = t on / T = D

Time (S)

D = 0.0 ~ 90% ; single pulse

1.E-01

1.E+00



# Marking Information

PDFN 3.3*3.3-8L	Marking Rule
Laser Marking	Line 1 : Device 100N07 Line 2 : Date Code YMMXXX Y : Year Code MM : Month Code XXX : Serial Number



# **Important Notice**

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